

		SEMESTER V				
Theory						
Course	UNIT	TOPICS	Cred	lits	Lec per Wee	tures ek
USPH501	Ι	Mathematical Methods in Physics	2	Л		1
	II	Mathematical Methods in Physics	2.0	5		-
	III	Thermal and Statistical Physics				
	IV	Thermal and Statistical Physics				
USPH502	Ι	Solid State Physics	•	-		
	II	Solid State Physics	2.	5		4
	III	Solid State Physics				
	IV	Solid State Physics				
USPH503	Ι	Atomic Physics		_		
	II	Atomic Physics	2.	5		4
	III	Molecular Physics				
	IV	Molecular Physics				
USPH504	Ι	Electrodynamics		_		
	II	Electrodynamics	2.	5		4
	III	Electrodynamics				
	IV	Electrodynamics				
Practicals						
USPHP05	Practi	cals of Course USPH501 + Course USPH5	502	2.	5	6
USPHP06	Practio	cals of Course USPH503 + Course USPH5	504	2.	5	6
	-	Project				-
USPHPR1	USF	2H501 + USPH502 + USPH503 + USPH50	)4	1	L	4

**T.Y.B.Sc. Physics Syllabus:** Credit Based Semester and Grading System to be implemented from the Academic year 2018-2019.

SEMESTER VI						
		Theory				
Course	UNIT	TOPICS	Crea	lits	Lec per We	tures ek
USPH601	Ι	Classical Mechanics	0	П		1
	II	Classical Mechanics	4.	σ		4
	III	Classical Mechanics				
	IV	Classical Mechanics				
USPH602	Ι	Electronics	•	_		
	II	Electronics	2.	5		4
	III	Electronics				
	IV	Electronics				
USPH603	Ι	Nuclear Physics	•	L		4
	II	Nuclear Physics	2.	5		4
	III	Nuclear Physics				
	IV	Nuclear Physics				
USPH604	Ι	Special Theory of Relativity	•	-		4
	II	Special Theory of Relativity	2.	5		4
	III	Special Theory of Relativity				
	IV	Special Theory of Relativity				
	L	Practicals				
USPH605	Practi	cals of Course USPH601 + Course USPH6	02	2.	.5	6
USPH606	Practi	cals of Course USPH603 + Course USPH6	04	2.	5	6
	I	Project	I			1
USPHPR2	USF	PH601 + USPH602 + USPH603 + USPH60	4	1	L	4

### SCHEME OF THEORY, PRACTICALS AND PROJECT EXAMINATION (SEM- V & VI)

I.	Theory: External Examination: 100 marks					
	Each theory paper shall be of <b>THREE</b> hours duration.					
	Each paper shall consist of FIVE questions. All questions are computed and will have internal options. Choice in papers has to be 1.5 times					
	Q – I :	From U	nit – I			
	Q – II : From Unit – II					
	Q – III :	From U	nit - III			
	Q – IV :	From U	nit - IV			
	Q – V :	Will con weightag	sist of questions from a ge of marks allotted to e	ll the FOUR Units with each Unit.	equal	
II.	<b>Practicals and Project:</b> The External Practical Examination will be conducted as per the following scheme.					
Sr. No.	Particula	ars of Ext	ternal Practical and P	roject Examination	Total Marks	
1	Laborato	ry Work	Experiment-1= 60 M	Experiment-2 = 60 M	120	
2	Journal		10	10	20	
3	Viva		10	10	20	
				Sub Total =	160	
III.	Project		Internal Examiner (20 M)	External Examiner (20 M)	40	
	1		1	Grand Total	200	

### Passing Criteria:

- 1. A student should be considered as passed in the practical examination provided he/she fulfills the following passing criteria
  - a. Minimum of 20 marks in each practical component i.e. **USPHP07** and **USPHP08**.
  - b. Minimum of 10 marks in Project Component
  - c. And cumulatively scoring 80 marks (i.e. 40 % of 200 marks)

Component	Maximum Marks	Minimum Passing Marks
USPHP07	80	20
USPHP08	80	20
Project 2	40	10
Total	200	80

### Scheme of Examination:

- 1. The University (external) examination for Theory and Practical shall be conducted at the end of each Semester and the evaluation of Project work at the end of the each Semester.
- 2. The candidate should appear for **THREE** Practical sessions of **three hours each** as part of his/her Practical course examination.
- 3. The candidates shall appear for external examination of 2 practical courses each carrying 80 marks and presentation of project work carrying 20 marks at the end of each semester.
- 4. The candidates shall also appear for internal presentation of project work carrying 20 marks at the end of each semester.
- 5. The candidate shall prepare and submit for practical examination a certified Journal based on the practical course with **6** experiments from each group.
- The certified journal must contain a minimum of 12 regular experiments (6 from each group), with minimum 5 demonstration experiments in semester VI. A separate index and certificate in journal is must for each semester course.
- 7. At the time of practical examination, the candidate must also submit the certified Project Report prepared as per the guidelines given in the Syllabus.

A candidate will be allowed to appear for the practical examination only if the candidate submits a certified journal of TYBSc Physics or a certificate from the Head of the Department to the effect that the candidate has completed the practical course of TYBSc Physics as per the minimum requirements and a project completion report duly certified by the project in-charge and Head of the Department.

**III. Visits: Visits** to industry, national research laboratories, and scientific exhibitions should be encouraged.

### **Theory Course - USPH502: Solid State Physics**

**Learning Outcomes:** On successful completion of this course students will be able to:

- 1. Understand the basics of crystallography, Electrical properties of metals, Band Theory of solids, demarcation among the types of materials, Semiconductor Physics and Superconductivity.
- 2. Understand the basic concepts of Fermi probability distribution function, Density of states, conduction in semiconductors and BCS theory of superconductivity.
- 3. Demonstrate quantitative problem solving skills in all the topics covered.

Unit - I	Crystal Physics	(15 lect.)		
The crystalline state, Basic definitions of crystal lattice, basis vectors, unit cell,				
primitive	and non-primitive cells. The fourteen Bravais lattices and	the seven		

crystal systems, elements of symmetry, nomenclature of crystal directions and crystal planes, Miller Indices, spacing between the planes of the same Miller indices, examples of simple crystal structures, The reciprocal lattice and X-ray diffraction.

Ref: Elementary Solid State Physics-Principles and Applications: M. Ali Omar, Pearson Education, 2012 : (1.1, 1.2, 1.3, 1.4, 1.5, 1.6, 1.7, 2.6)

Unit -II	Electrical properties of metals	(15 lect.)

- 1. Classical free electron theory of metals, Drawbacks of classical theory, Relaxation time, Collision time and mean free path
- 2. Quantum theory of free electrons, Fermi Dirac statistics and electronic distribution in solids, Density of energy states and Fermi energy, The Fermi distribution function, Heat capacity of the Electron gas, Mean energy of electron gas at 0 K, Electrical conductivity from quantum mechanical considerations, Failure of Sommerfeld's free electron Theory
- 3. Thermionic Emission

	Ref.: Solid State Physics: S. O. Pillai, New Age International. 6th Ed.					
	Chapter 6: II, III, IV, V, XIV, XV, XVI, XVII, XVIII, XX, XXXV, XXXI.					
Ur	it -III	Band Theory of Solids and Conduction in Semiconductors	(15 lect.)			
1.	<ul> <li>Band theory of solids, The Kronig- Penney model (Omit eq. 6.184 to 6.188), Brillouin zones, Number of wave functions in a band, Motion of electrons in a one-dimensional periodic potential, Distinction between metals, insulators and intrinsic semiconductors.</li> <li>Ref.: Solid State Physics: S. O. Pillai, New Age International, 6<sup>th</sup> Ed.</li> <li>Chapter 6: XXXVI, XXXVII, XXXVIII, XXXIX, XXXX, XXXXI</li> <li>Electrons and Holes in an Intrinsic Semiconductor, Conductivity of a Semiconductor, Carrier concentrations in an intrinsic semiconductor, Donor</li> </ul>					
	extrins equatio Ref.: El (3 <sup>rd</sup> Ed.	ic semiconductors, Diffusion, Carrier lifetime, The on, Hall Effect. ectronic Devices and Circuits: Millman, Halkias & Satyabra ) Tata McGraw Hill.: 4.1 to 4.10.	continuity ta Jit.			
Ur	it -IV	Diode Theory and superconductivity	(15 lect.)			
1.	Semico The p-1 The cu diode depend	nductor-diode Characteristics: Qualitative theory of the p- n junction as a diode, Band structure of an open-circuit p- rrent components in a p-n junction diode, Quantitative the currents, The Volt-Ampere characteristics, The te lence of p-n characteristics, Diode resistance.	n junction, n junction, eory of p-n emperature			
	Ref.: El (3 <sup>rd</sup> Ed	ectronic Devices and Circuits: Millman, Halkias & Satyabra ) Tata McGraw Hill.: 5.1 to 5.8	ata Jit.			
2.	Superc destruc Londor Superc	onductivity: Experimental Survey, Occurrence of Superco ction of superconductivity by magnetic field, The Meiss a equation, BCS theory of superconductivity, Type I ar onductors, Vortex state.	nductivity, ner effect, nd Type II			
	Ref.: In	troduction to Solid State Physics-Charles Kittel, 7th Ed. Joh	nn Wiley &			

Sons: Topics from Chapter 12.

## Main References:

1.	Elementary Solid State Physics-Principles and Applications: M.Ali Omar, Pearson Education, 2012.
2.	Solid State Physics: S. O. Pillai, New Age International, 6th Ed.
3.	Electronic Devices and Circuits: Millman, Halkias & Satyabrata Jit. (3 <sup>rd</sup> Ed.) Tata McGraw Hill.
4.	Introduction to Solid State Physics - Charles Kittel, 7 <sup>th</sup> Ed. John Wiley & Sons.
5.	Modern Physics and Solid State Physics: Problems and solutions New Age International.
Add	itional References:
1.	Solid State Physics: A. J. Dekker, Prentice Hall.
2.	Electronic Properties of Materials: Rolf Hummel, 3rd Ed. Springer.
3.	Semiconductor Devices: Physics and Technology, 2 <sup>nd</sup> Ed. John Wiley & Sons.
4.	Solid State Physics: Ashcroft & Mermin, Harcourt College Publisher.

## **Theory Course – USPH602: Electronics**

### Learning Outcome:

On successful completion of this course students will be able to:

- 1. Understand the basics of semiconductor devices and their applications.
- 2. Understand the basic concepts of operational amplifier: its prototype and applications as instrumentation amplifier, active filters, comparators and waveform generation.
- 3. Understand the basic concepts of timing pulse generation and regulated power supplies
- 4. Understand the basic electronic circuits for universal logic building blocks and basic concepts of digital communication.
- 5. Develop quantitative problem solving skills in all the topics covered.

Unit - I	(15 lect.)
1. Field transcond Transcond multiplexe	effect transistors: JFET: Basic ideas, Drain curve, The uctance curve, Biasing in the ohmic region and the active region, luctance, JFET common source amplifier, JFET analog switch, er, voltage controlled resistor, Current sourcing.
2. MOSF characteri	ET: Depletion and enhancement mode, MOSFET operation and stics, digital switching.
3. SCR – Gate Trigg wave recti	construction, static characteristics, Analysis of the operation of SCR, gering Characteristics, Variable half wave rectifier and Variable full fier, Current ratings of SCR.
4. UJT: relaxation	Construction, Operation, characteristics and application as a oscillator.
1. MB: 2. MB: 3. AM:	13.1 to 13.9 14.1, 14.2, 14.4, 14.6. 28.1, 28.5
Unit -II	(15 lect.)
1. Differer	ntial Amplifier using transistor: The Differential Amplifier, DC and AC
analysis o	of a differential amplifier, Input characteristic-effect of input bias,
offset curr	ent and input offset voltage on output, common mode gain, CMRR.

2. Op Amp Applications: Log amplifier, Instrumentation amplifiers, Voltage controlled current sources (grounded load), First order Active filters, Astable using OP AMP, square wave and triangular wave generator using OP AMP, Wein-bridge oscillator using OP AMP, Comparators with Hysteresis, Window Comparator.

1. MB: 17.1 to 17.5

2. MB: 20.5, 20.8, 21.4, 22.2, 22.3, 22.7, 22.8, 23.

# Unit -III (15 lect.)

1. Transistor Multivibrators: Astable, Monostable and Bistable Multivibrators, Schmitt trigger.

2. 555 Timer: Review Block diagram, Monostable and Astable operation Voltage Controlled Oscillator, Pulse Width modulator, Pulse Position Modulator, Triggered linear ramp generator.

3. Regulated DC power supply: Supply characteristics, series voltage regulator, Short circuit protection (current limit and fold back) Monolithic linear IC voltage Regulators. (LM 78XX, LM 79XX, LM 317, LM337).

- 1. AM: 18.11
- 2. KVR: 14.5.2.1, 14.5.2.5, 14.5.2.6, 14.5.4.1
- 3. MB: 23.8, 23.9
- 4. MB: 24.1, 24.3, 24.4

### Unit -IV

(15 lect.)

1. Logic families: Standard TTL NAND, TTL NOR, Open collector gates, Three state TTL devices, MOS inverters, CMOS NAND and NOR gates, CMOS characteristics.

2. Digital Communication Techniques: Digital Transmission of Data, Benefits of Digital Communication, Disadvantages of Digital Communication, Parallel and Serial Transmission, Pulse Modulation, Comparing Pulse-Modulation Methods ( PAM, PWM, PPM), Pulse-Code Modulation.

1. ML: 6.2, 6.4, 6.6, 6.7, 7.2 to 7.4.

2. LF: 7.1, 7.2, 7.4

Refe	rences
1.	MB: Electronic Principles, Malvino & Bates -7th Ed TMH Publication.
2.	AM: Electronic Devices and Circuits, Allen Mottershead -PHI Publication.
3.	KVR: Functional Electronics, K.V. Ramanan-TMH Publication.
4.	ML: Digital Principles and Applications, Malvino and Leach (4th Ed)(TMH).
5.	LF: Communication Electronics: Principles and applications, Louis E Frenzel 4 <sup>th</sup> edition TMH Publications.